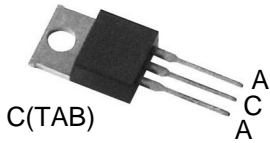
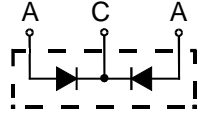


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Ultra Fast Recovery Epitaxial Diodes

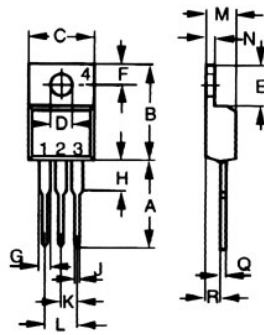


C(TAB)



A=Anode, C=Cathode, TAB=Cathode

Dimensions TO-220AB



Dim.	Inches		Millimeter	
	Min.	Max.	Min.	Max.
A	0.500	0.550	12.70	13.97
B	0.580	0.630	14.73	16.00
C	0.390	0.420	9.91	10.66
D	0.139	0.161	3.54	4.08
E	0.230	0.270	5.85	6.85
F	0.100	0.125	2.54	3.18
G	0.045	0.065	1.15	1.65
H	0.110	0.230	2.79	5.84
J	0.025	0.040	0.64	1.01
K	0.100	BSC	2.54	BSC
M	0.170	0.190	4.32	4.82
N	0.045	0.055	1.14	1.39
Q	0.014	0.022	0.35	0.56
R	0.090	0.110	2.29	2.79

	V_{RSM}	V_{RRM}
	V	V
SUR1660CT	600	600

Symbol	Test Conditions	Maximum Ratings	Unit
I_{FRMS}	$T_{VJ}=T_{VJM}$	16	A
I_{FAVM}	$T_C=115^\circ\text{C}$; rectangular, $d=0.5$	8	
I_{FRM}	$t_p < 10\mu\text{s}$; rep. rating, pulse width limited by T_{VJM}	130	
I_{FSM}	$T_{VJ}=45^\circ\text{C}$	$t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	A
	$T_{VJ}=150^\circ\text{C}$	$t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	
I^2t	$T_{VJ}=45^\circ\text{C}$	$t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	A^2s
	$T_{VJ}=150^\circ\text{C}$	$t=10\text{ms}$ (50Hz), sine $t=8.3\text{ms}$ (60Hz), sine	
T_{VJ}		-40...+150	$^\circ\text{C}$
T_{VJM}		150	
T_{stg}		-40...+150	
P_{tot}	$T_C=25^\circ\text{C}$	50	W
M_d	Mounting torque	0.4...0.6	Nm
Weight		2	g

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Symbol	Test Conditions	Characteristic Values		Unit
		typ.	max.	
I_R	$T_{VJ}=25^{\circ}\text{C}; V_R=V_{RRM}$		20	uA
	$T_{VJ}=25^{\circ}\text{C}; V_R=0.8 \cdot V_{RRM}$		10	uA
	$T_{VJ}=125^{\circ}\text{C}; V_R=0.8 \cdot V_{RRM}$		1.5	mA
V_F	$I_F=8\text{A}; T_{VJ}=150^{\circ}\text{C}$		1.3	V
	$T_{VJ}=25^{\circ}\text{C}$		1.5	
V_{TO}	For power-loss calculations only		0.98	V
r_T	$T_{VJ}=T_{VJM}$		28.7	m Ω
R_{thJC} R_{thCK} R_{thJA}		0.5	2.5	K/W
			60	
t_{rr}	$I_F=1\text{A}; -di/dt=50\text{A}/\mu\text{s}; V_R=30\text{V}; T_{VJ}=25^{\circ}\text{C}$	35	50	ns
I_{RM}	$V_R=540\text{V}; I_F=15\text{A}; -di_F/dt=100\text{A}/\mu\text{s}; L<0.05\mu\text{H}; T_{VJ}=100^{\circ}\text{C}$	2.5	2.8	A

FEATURES

- * International standard package JEDEC TO-220AB
- * Planar passivated chips
- * Very short recovery time
- * Extremely low switching losses
- * Low I_{RM}-values
- * Soft recovery behaviour

APPLICATIONS

- * Antiparallel diode for high frequency switching devices
- * Antisaturation diode
- * Snubber diode
- * Free wheeling diode in converters and motor control circuits
- * Rectifiers in switch mode power supplies (SMPS)
- * Inductive heating and melting
- * Uninterruptible power supplies (UPS)
- * Ultrasonic cleaners and welders

ADVANTAGES

- * High reliability circuit operation
- * Low voltage peaks for reduced protection circuits
- * Low noise switching
- * Low losses
- * Operating at lower temperature or space saving by reduced cooling

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Ultra Fast Recovery Epitaxial Diodes

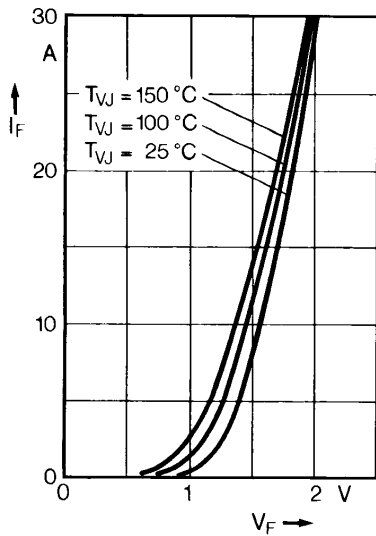


Fig. 1 Forward current versus voltage drop.

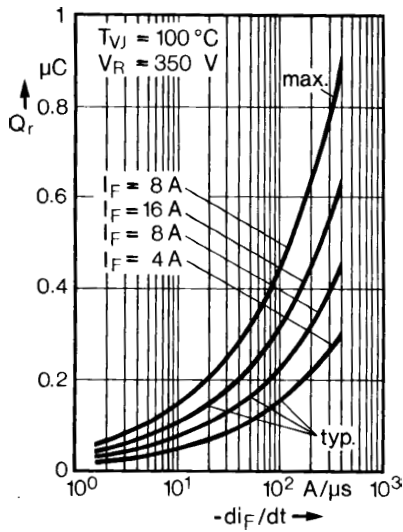


Fig. 2 Recovery charge versus $-di_F/dt$.

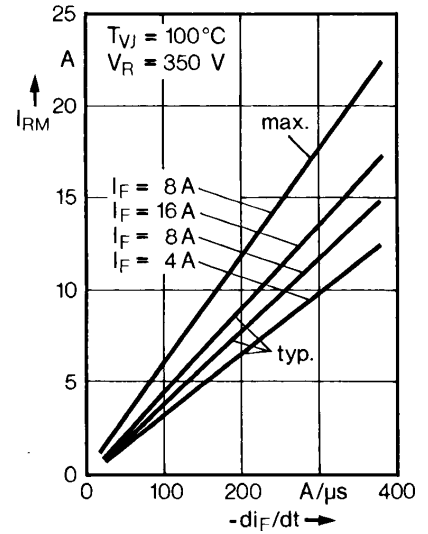


Fig. 3 Peak reverse current versus $-di_F/dt$.

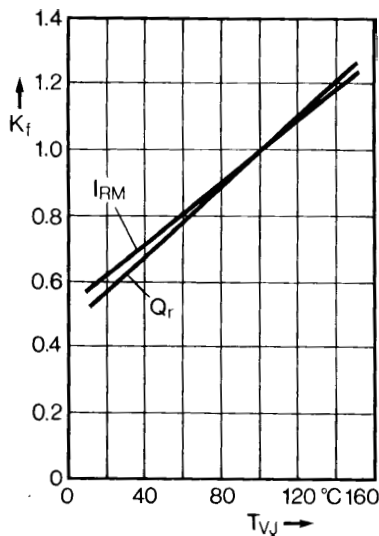


Fig. 4 Dynamic parameters versus junction temperature.

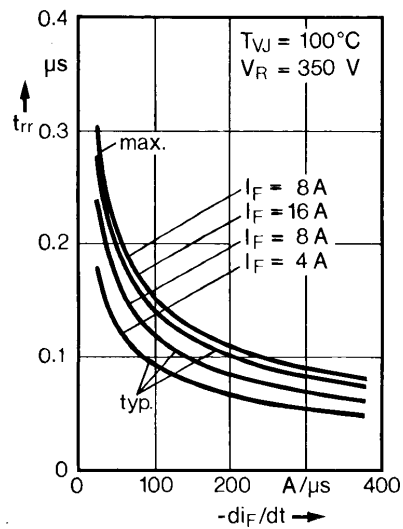


Fig. 5 Recovery time versus $-di_F/dt$.

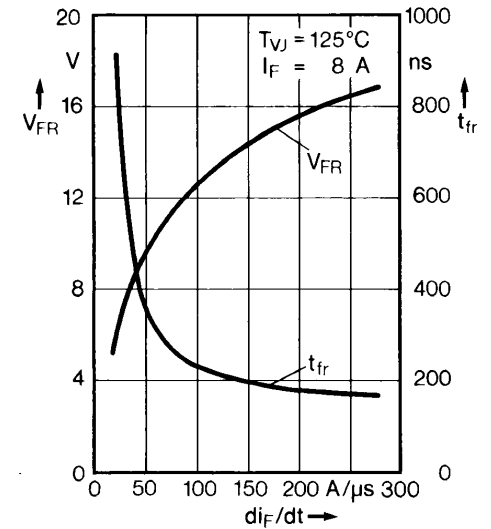


Fig. 6 Peak forward voltage versus di_F/dt .

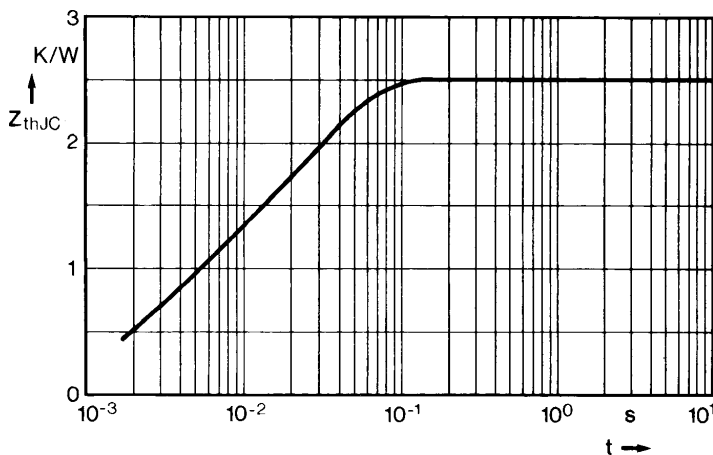


Fig. 7 Transient thermal impedance junction to case.